

POST-PLASMA PROCESSING WAFER CLEANING METHOD AND SYSTEM

ABSTRACT OF THE DISCLOSURE

5 A method and system are provided for cleaning a surface of a semiconductor
wafer following a plasma etching operation. The method is preferably performed inside a
brush box and involves wetting the surface of the semiconductor wafer by using a non-
splash rinse technique. The non-splash rinse technique is configured to quickly and
evenly saturate the surface of the semiconductor wafer with a liquid (preferably de-
10 ionized water). The wetting will therefore remove unwanted residues that could
otherwise further cause stains or scratches on the wafer surface. Following the wetting
operation, the surface of the wafer may be finely scrubbed with a cleaning brush that
applies a chemical solution to the surface of the wafer. A second cleaning brush may also
be implemented so that both the top and the bottom surfaces of the wafer may be finely
15 scrubbed.